

SMB Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

■Features 特点

Low forward voltage drop 低正向压降

High current capability 高电流能力

Surface mount device 表面贴装器件

Case 封装:SMB(DO-214AA)



■Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SS84B	SS86B	SS810B	SS815B	SS820B	Unit 单位
Marking 印字		SS84	SS86	SS810	SS815	SS820	
Peak Reverse Voltage 反向峰值电压	V_{RRM}	40	60	100	150	200	V
DC Reverse Voltage 直流反向电压	V_R	40	60	100	150	200	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	28	42	70	105	140	V
Forward Rectified Current 正向整流电流	I_F	8					A
Peak Surge Current 峰值浪涌电流	I_{FSM}	150					A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	55					$^{\circ}\text{C}/\text{W}$
Junction Temperature 结温	T_J	150					$^{\circ}\text{C}$
Storage Temperature 储藏温度	T_{stg}	-55to+150					$^{\circ}\text{C}$

■Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SS84B	SS86B	SS810B	SS815B-SS820B	Unit 单位	Condition 条件
Forward Voltage 正向电压	V _F	0.55	0.70	0.85	0.92	V	I _F =8A
Reverse Current 反向电流	I _R (25℃) (100℃)	0.1 5		0.02 2		mA	V _R =V _{RRM}
Diode Capacitance 二极管电容	C _D	350				pF	V _R =4V, f=1MHz

■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

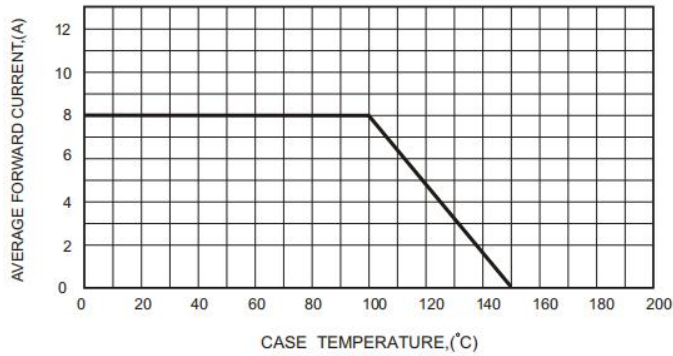


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

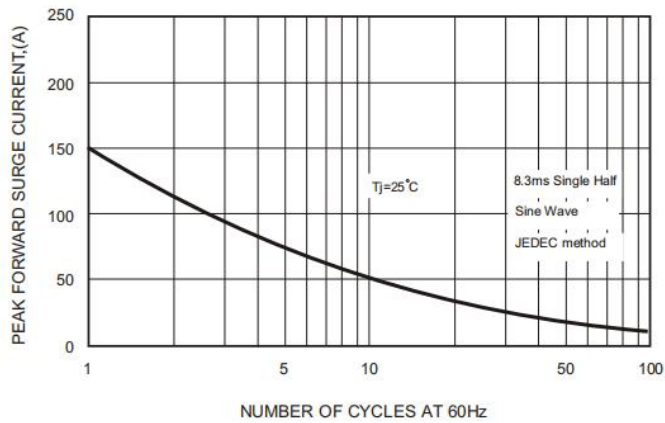


FIG.4-TYPICAL JUNCTION CAPACITANCE

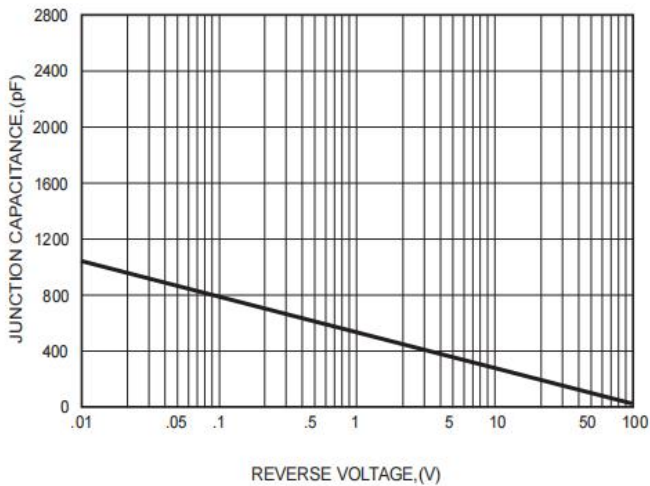


FIG.2-TYPICAL FORWARD CHARACTERISTICS

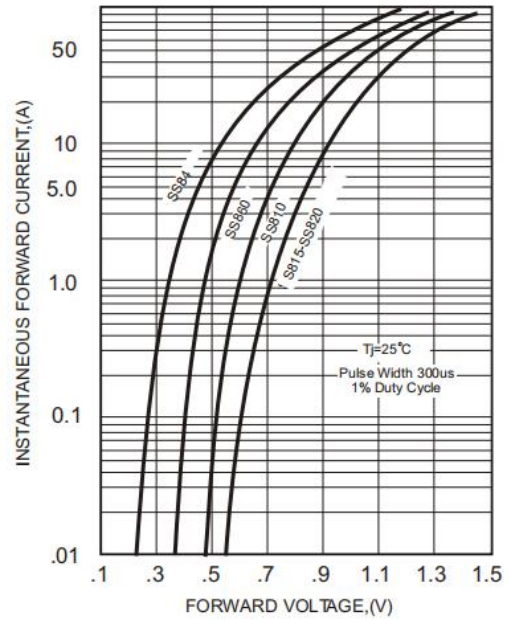
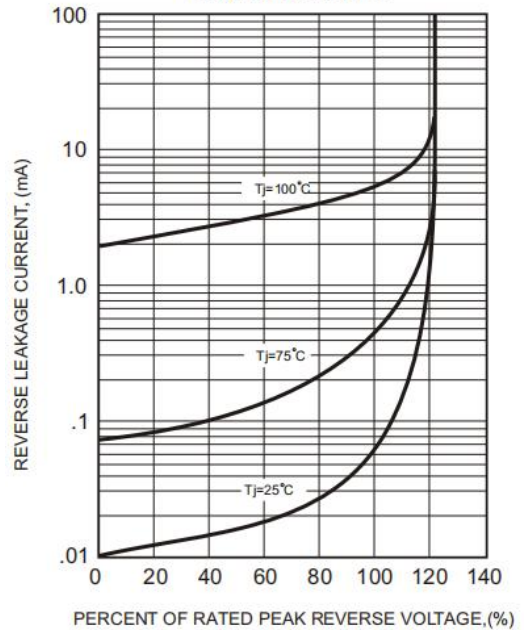
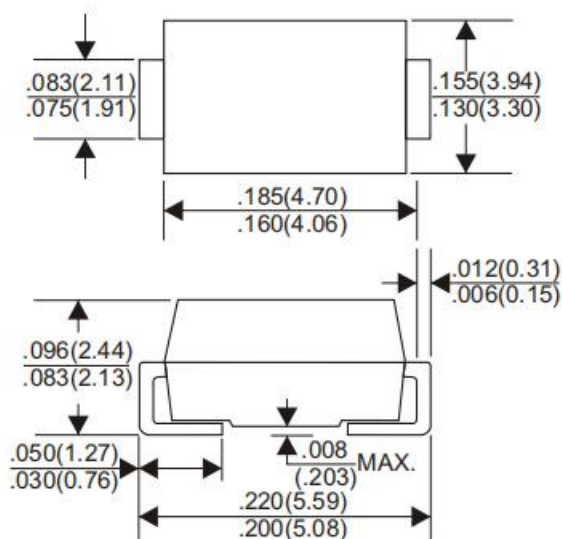


FIG.5 - TYPICAL REVERSE CHARACTERISTICS



■Dimension 外形封装尺寸

DO-214AA(SMB)



Dimensions in inches and (millimeters)